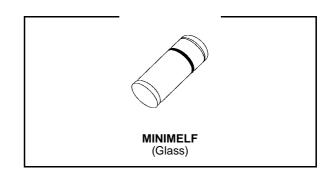


SMALL SIGNAL SCHOTTKY DIODE



DESCRIPTION

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarly intended for high level UHF/VHF detection and pulse application with broad dynamic range.

ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	60	V
I _F	Forward Continuous Current	15	mA
I _{FSM}	Surge non Repetitive Forward Current	50	mA
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to 200 -65 to 200	°C
TL	Maximum Temperature for Soldering during 1	260	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-l)}	Junction-leads	400	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions				Тур.	Max.	Unit
V_{BR}	T _{amb} = 25°C	$I_R = 10\mu A$		60			>
V _F *	T _{amb} = 25°C	$I_F = 1mA$				0.41	٧
	T _{amb} = 25°C	$I_F = 15mA$				1	
I _R *	T _{amb} = 25°C	V _R = 50V				0.2	μΑ

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions				Тур.	Max.	Unit
С	$T_{amb} = 25^{\circ}C$	$V_R = 0V$	f = 1MHz			2.2	pF
τ	T _{amb} = 25°C	$I_F = 5mA$	Krakauer Method			100	ps

^{*} Pulse test: $t_p \le 300 \mu s \delta < 2\%$.

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

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Figure 1. Forward current versus forward voltage (typical values).

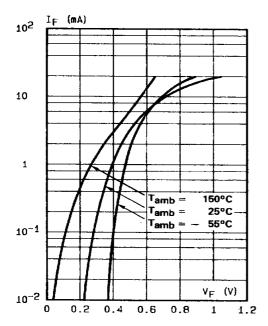


Figure 2. Capacitance C versus reverse applied voltage $V_{\mbox{\scriptsize R}}$ (typical values).

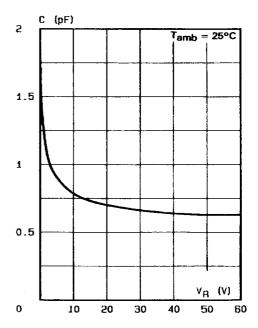


Figure 3. Reverse current versus ambient temperature.

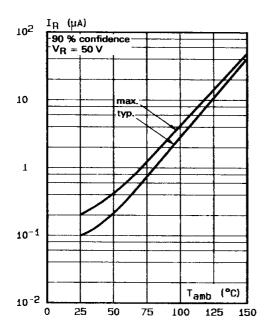
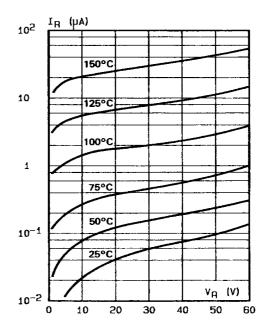


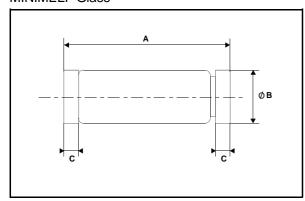
Figure 4. Reverse current versus continuous reverse voltage (typical values).



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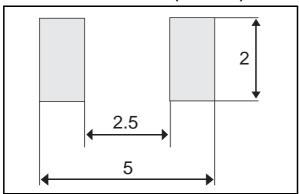
PACKAGE MECHANICAL DATA

MINIMELF Glass



	DIMENSIONS						
REF.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	3.30	3.40	3.6	0.130	0.134	0.142	
В	1.59	1.60	1.62	0.063	0.063	0.064	
С	0.40	0.45	0.50	0.016	0.018	0.020	
D		1.50			0.059		

FOOT PRINT DIMENSIONS (Millimeter)



Marking: ring at cathode end. Weight: 0.05g

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